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Folded down-conversion mixer for a 60 GHz receiver architecture in 65-nm CMOS technology

Key words: Folded mixer, Current reuse, Low power, Inductorless design, Direct conversion

Contact: Najam Muhammad AMIN,

E-mail: najam.m.amin@seu.edu.cn

 ORCID: <http://orcid.org/0000-0002-9419-0380>

Introduction

- The conventional Gilbert mixer is unsuitable for low supply voltages due to its stacked architecture.
- To resolve the problem of voltage headroom and achieve an optimum performance from the mixer in terms of high conversion gain and low noise figure, folded mixer topology must be employed.
- A folded mixer design for a 60 GHz receiver in a 65 nm LP-CMOS process has been presented in this work.

The 60 GHz receiver with emphasis on this work

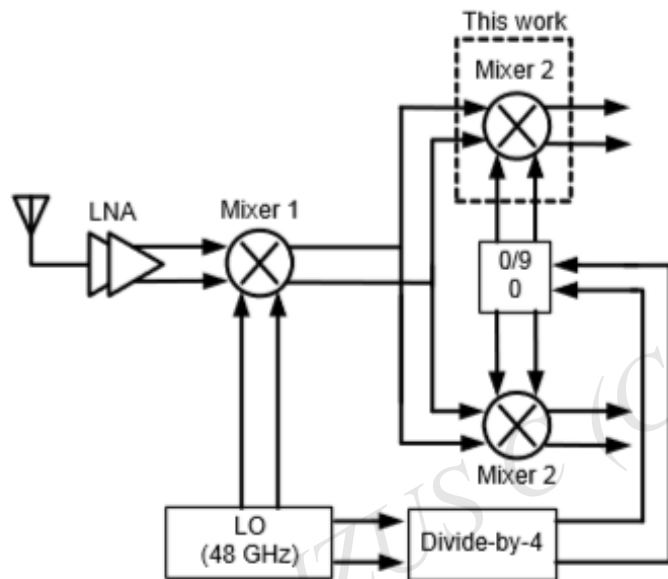


Fig. 1 The 60 GHz receiver architecture with emphasis on this work

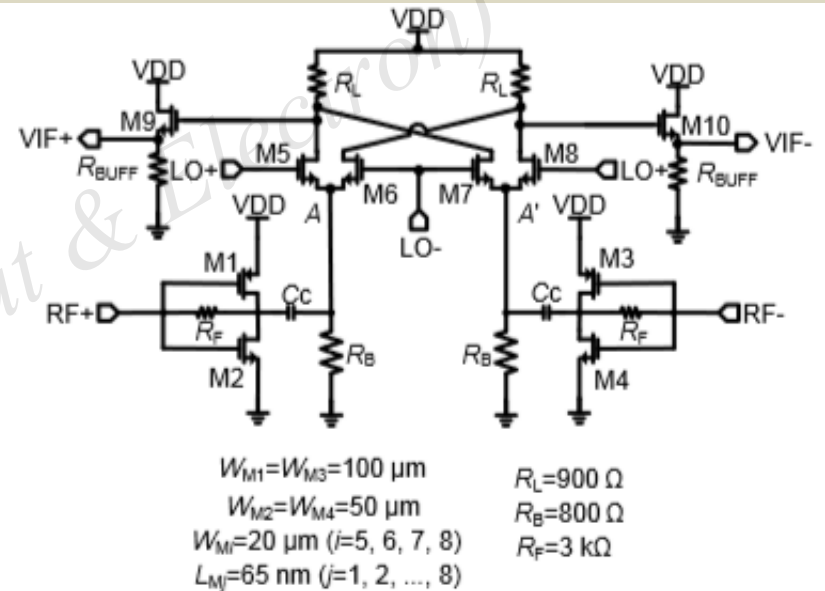


Fig. 2 Schematic of the proposed folded mixer design along with component values

Chip micrograph

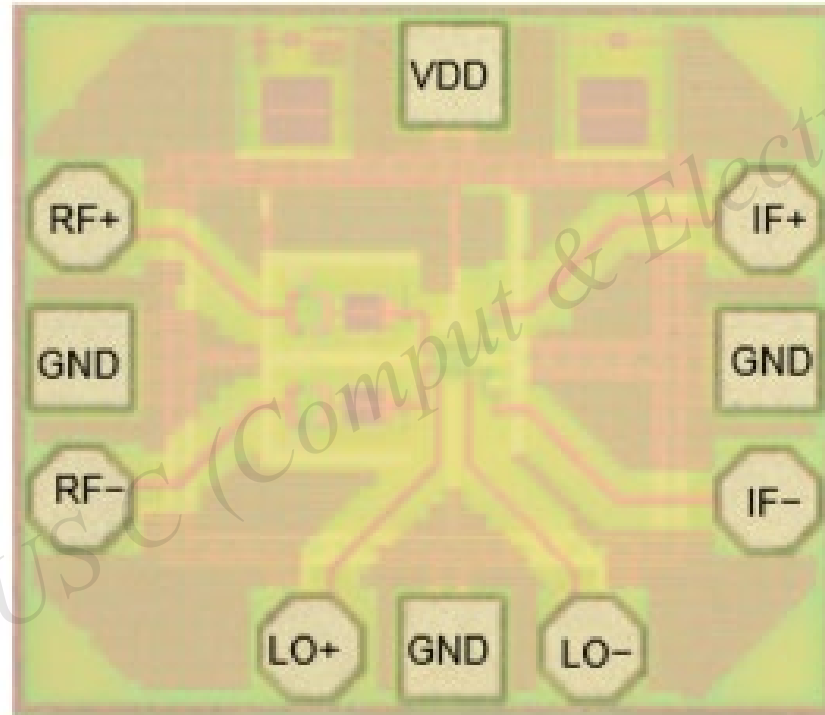


Fig. 7 Chip micrograph of the proposed folded mixer

Measurement results (1)

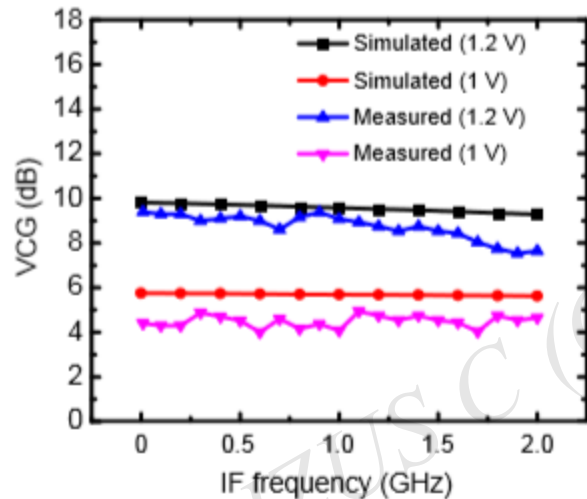


Fig. 8 Measured and simulated voltage conversion gains for VDD=1.2 V and 1 V

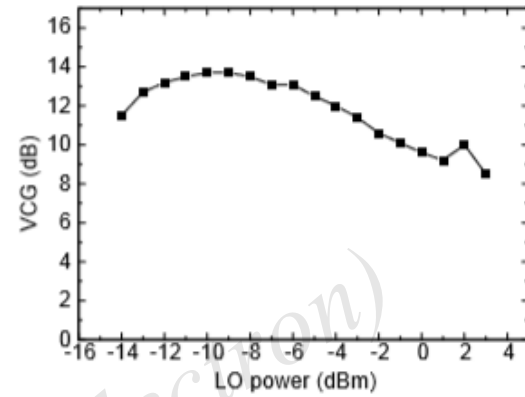


Fig. 9 Conversion gain variation with respect to LO power at an IF=10 MHz

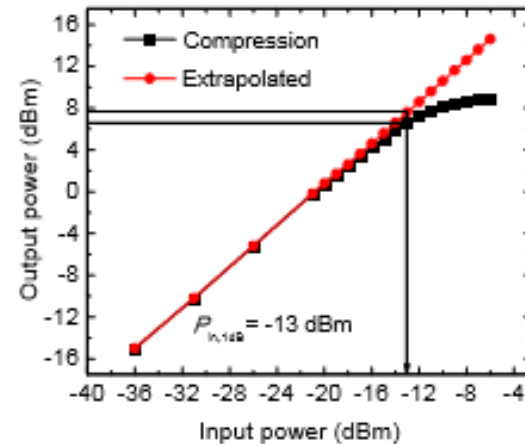


Fig. 10 $P_{in,1dB}$ at an IF of 10 MHz ($f_{RF}=12.01$ GHz, $f_{LO}=12$ GHz)

Measurement results (2)

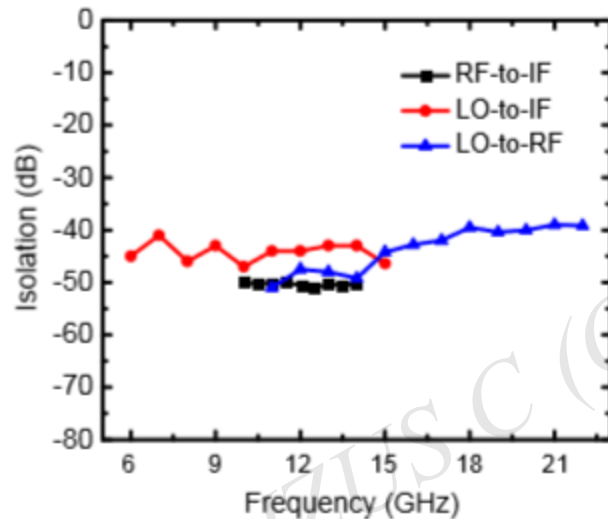


Fig. 11 Isolation characteristics of the proposed mixer (baluns with different frequency ranges were employed to measure isolation)

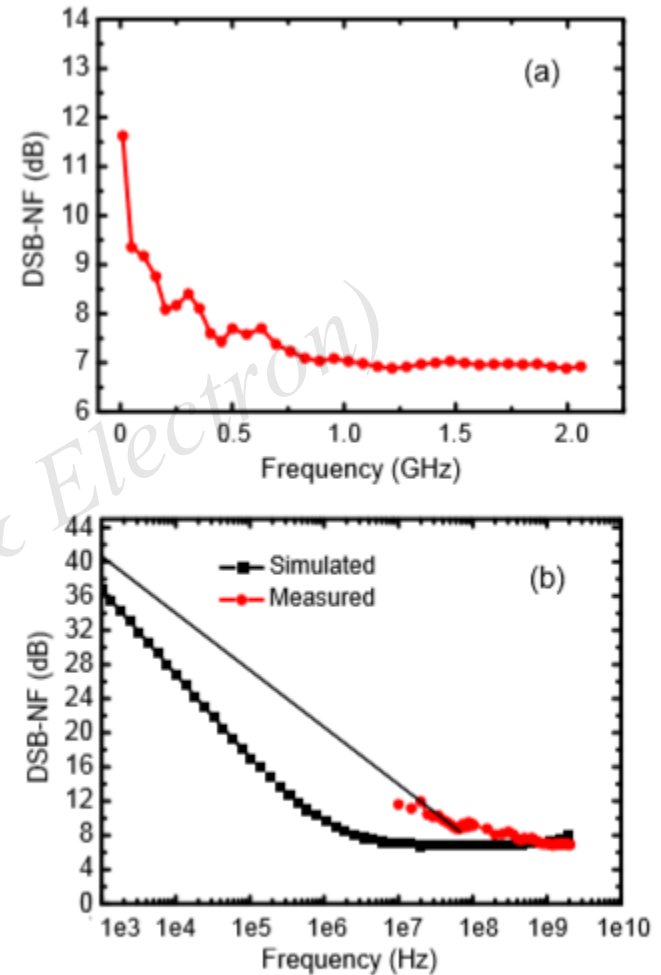


Fig. 13 Double sideband noise figure (DSB-NF): (a) linear IF axis; (b) simulated NF along with measured and extrapolated NF curves in a log-frequency axis

Performance comparison

Table B1 Performance summary with comparison to other works

Parameter	Value/Description						This work
	Hermann <i>et al.</i> (2005)	Klumperink <i>et al.</i> (2004)	Furuta <i>et al.</i> (2007)	Poobuapheun <i>et al.</i> (2007)*	Safarian <i>et al.</i> (2005)	Hampel <i>et al.</i> (2010)	
Process	0.13 μm CMOS	0.18 μm CMOS	0.13 μm CMOS	0.13 μm CMOS	0.18- μm CMOS	65 nm CMOS	65 nm CMOS
RF frequency (GHz)	2.1–3	0.3–4	0.85–2.1	0.7–2.5	3–8.72	1–10.5	10.25–13.75
CG_{max} (dB)	5.4	11	13.2	38	5	14.5	≈ 10
$P_{\text{in,1dB}}$ (dBm)	–9.2	NA	–6	–25.8	NA	–13.8	–13
IIP3 (dBm)	3.5	4.1	4.5	11	5	–4.2	–3.4**
NF_{min} (dB)	14.8 (SSB)	14 (SSB)	12.3 (DSB)	10 (DSB)	6.8	6.5 (DSB)	7 (DSB)
P_{DC} (mW)	1.6	6.6	8.25	24	10.4	14.4	6
VDD (V)	0.6	1	1.5	1.5	1.8	1.2	1.2
FOM*** (dB)	9.45	10.3	9.37	22.6	10	9.037	10.5
Area (mm^2)	NA	0.0048	NA	NA	1.624	0.011	0.017

* Including narrowband opamp; ** $\text{IIP3} = P_{1\text{dB}} + 9.6$ (Razavi, 1988); *** $\text{FOM} = 10 \lg \left(\frac{10^{G/20} \cdot 10^{(\text{IIP3}-10)/20}}{10^{3\text{IIP3}/10} P(\text{mW})} \right)$

Conclusions

- The folded mixer employing an ac-coupled self-biased current reuse topology for its transconductance stage shows good performance in terms of conversion gain, noise figure, and linearity.
- The proposed mixer achieves a competitive (slightly better) FOM compared to those proposed in the recent literature.